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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SA1029, 2SA1030

Silicon PNP Epitaxial

RENESAS

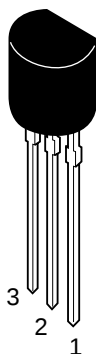
ADE-208-1004A (Z)
2nd. Edition
Mar. 2001

Application

- Low frequency amplifier
- Complementary pair with 2SC458 and 2SC2308

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SA1029, 2SA1030

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	2SA1029	2SA1030	Unit
Collector to base voltage	V_{CBO}	-30	-55	V
Collector to emitter voltage	V_{CEO}	-30	-50	V
Emitter to base voltage	V_{EBO}	-5	-5	V
Collector current	I_C	-100	-100	mA
Emitter current	I_E	100	100	mA
Collector power dissipation	P_C	300	300	mW
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-55 to +150	°C

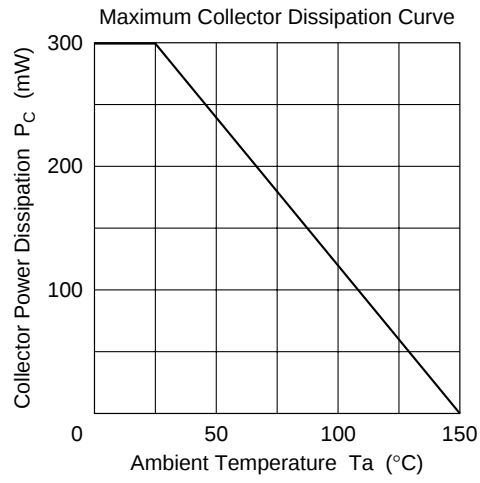
Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SA1029			2SA1030			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-30	—	—	-55	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-30	—	—	-50	—	—	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-0.5	—	—	-0.5	μA	$V_{CB} = -18 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	-0.5	—	—	-0.5	μA	$V_{EB} = -2 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	100	—	500	100	—	320		$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$
Base to emitter voltage	V_{BE}	—	—	-0.8	—	—	-0.8	V	$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.2	—	—	-0.2	V	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$
Gain bandwidth product	f_T	200	280	—	200	280	—	MHz	$V_{CB} = -12 \text{ V}, I_C = -2 \text{ mA}$
Collector output capacitance	C_{ob}	—	3.3	4.0	—	3.3	4.0	pF	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

Note: 1. The 2SA1029 and 2SA1030 are grouped by h_{FE} as follows.

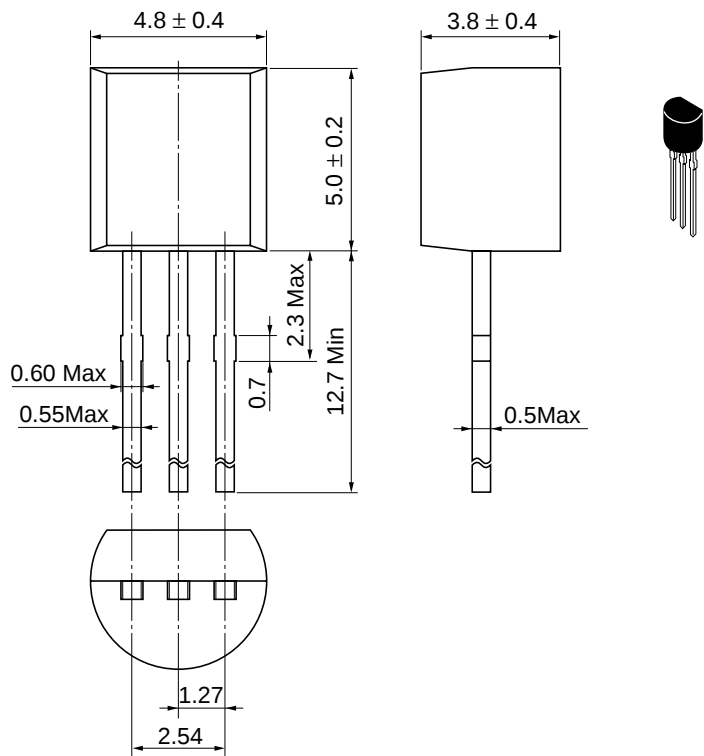
	B	C	D
2SA1029	100 to 200	160 to 320	250 to 500
2SA1030	100 to 200	160 to 320	—

See characteristic curves of 2SA1052.



Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.25 g

Cautions

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